

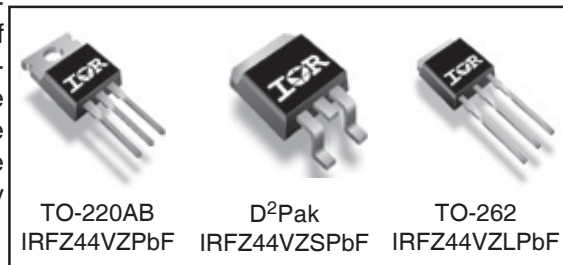
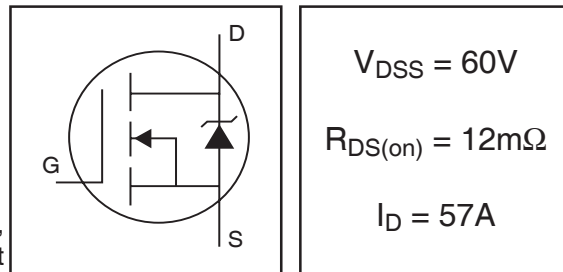
**Features**

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free

**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

**HEXFET® Power MOSFET**



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	57	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	40	
$I_{DM}$	Pulsed Drain Current ①	230	
$P_D @ T_C = 25^\circ C$	Power Dissipation	92	W
	Linear Derating Factor	0.61	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	73	mJ
$E_{AS}$ (Tested)	Single Pulse Avalanche Energy Tested Value ⑥	110	
$I_{AR}$	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw ⑦	10 lbf•in (1.1N•m)	

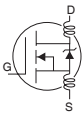
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface ⑦	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑦	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	—	40	

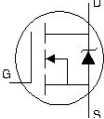
# IRFZ44VZS/LPbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

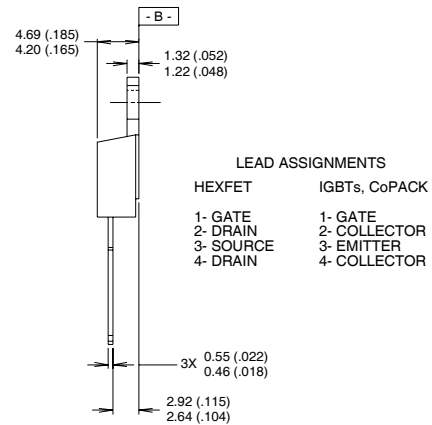
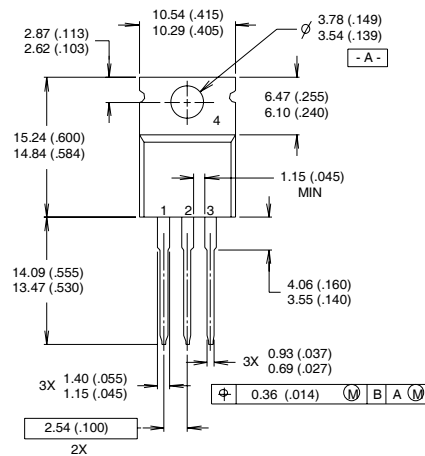
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.061	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	9.6	12	mΩ	$V_{GS} = 10V, I_D = 34A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
gfs	Forward Transconductance	25	—	—	V	$V_{DS} = 25V, I_D = 34A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 60V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	43	65	nC	$I_D = 34A$
$Q_{gs}$	Gate-to-Source Charge	—	11	—		$V_{DS} = 48V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	18	—		$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = 30V$
$t_r$	Rise Time	—	62	—		$I_D = 34A$
$t_{d(off)}$	Turn-Off Delay Time	—	35	—		$R_G = 12\ \Omega$
$t_f$	Fall Time	—	38	—		$V_{GS} = 10V$ ③
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1690	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	270	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	130	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	1870	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	260	—		$V_{GS} = 0V, V_{DS} = 48V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	510	—		$V_{GS} = 0V, V_{DS} = 0V\ \text{to}\ 48V$ ④

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	57	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	230		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 34A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	23	35	ns	$T_J = 25^\circ\text{C}, I_F = 34A, V_{DD} = 30V$
$Q_{rr}$	Reverse Recovery Charge	—	17	26	nC	$di/dt = 100A/\mu\text{s}$ ③
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note: "P" in assembly line position indicates "Lead-Free"**

